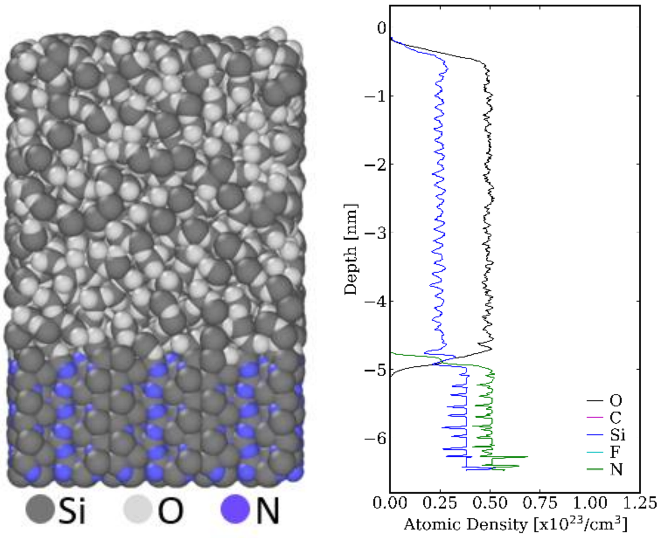
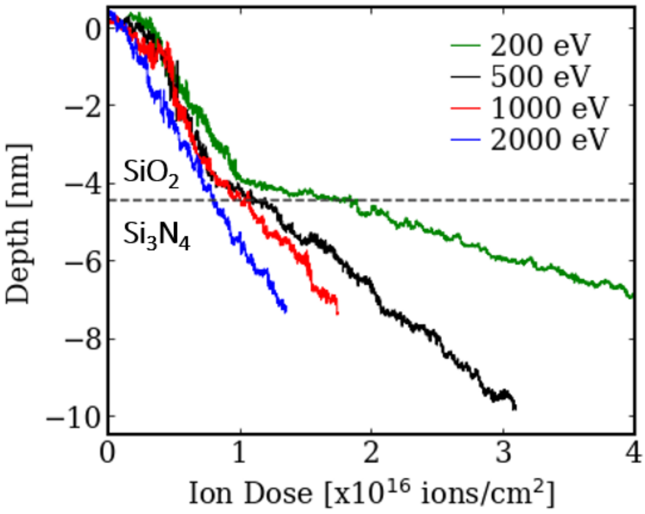
Supplementary Document



Initial oxide-nitride substrate with 4nm x 4nm x 5nm SiO_2 layer on top of Si_3N_4 and the corresponding depth profile.



Change in depth of oxide-nitride substrate as a function of CF_3^+ ion dose with 200eV, 500eV, 1000eV and 2000eV energy.